

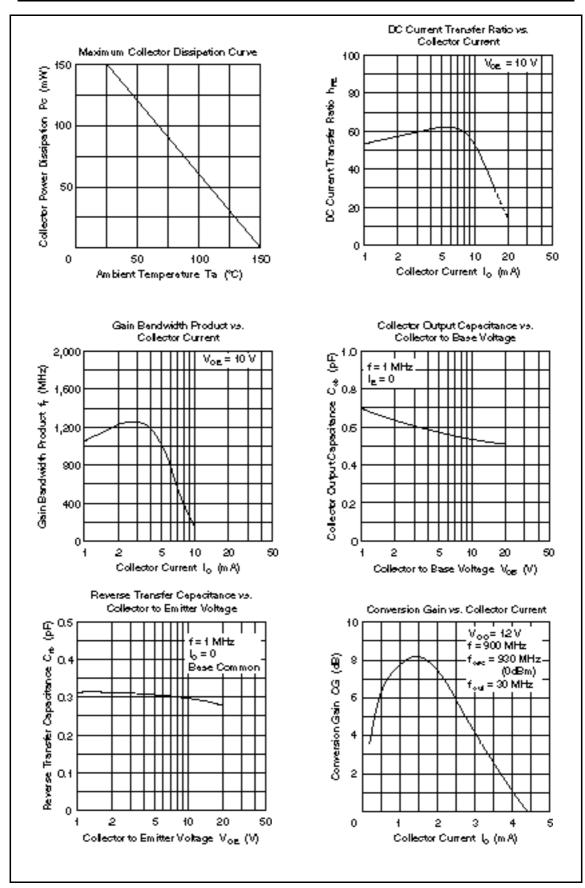
#### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	30	V
Collector to emitter voltage	V <sub>CEO</sub>	25	V
Emitter to base voltage	V <sub>EBO</sub>	4	V
Collector current	I <sub>c</sub>	20	mA
Collector power dissipation	Pc	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

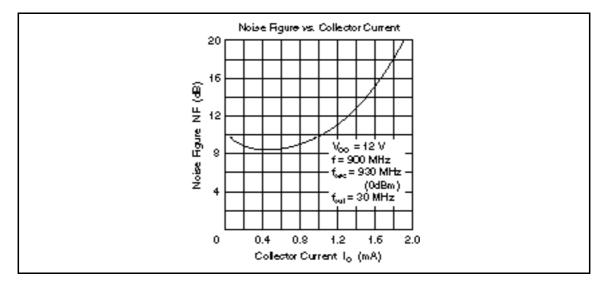
#### **Electrical Characteristics** (Ta = 25°C)

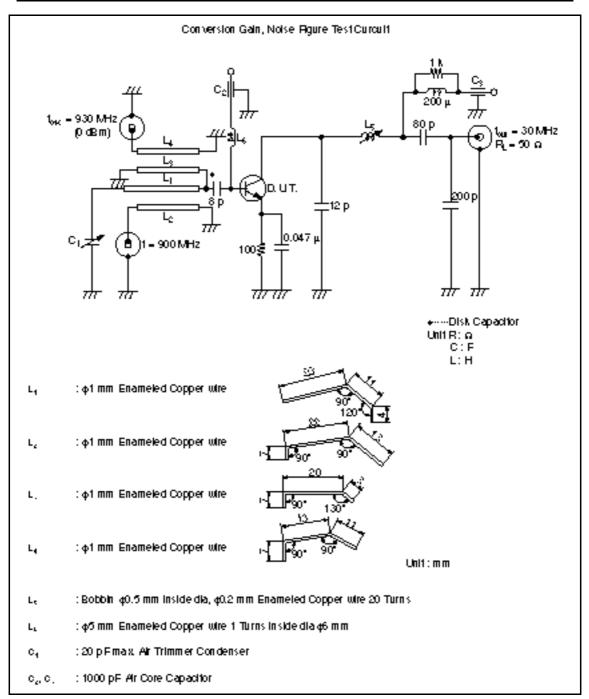
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	25	_	_	V	$I_c = 1 \text{ mA}, \text{ R}_{\text{BE}} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	_	—	V	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>			0.5	μA	$V_{CB} = 10 \text{ V}, \text{ I}_{C} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	5	V	$I_{c} = 10 \text{ mA}, I_{B} = 1 \text{ mA}$
DC current transfer ratio	h <sub>FE</sub>	30	60			$V_{ce}$ = 10 V, $I_{c}$ = 3 mA
Gain bandwidth product	f <sub>T</sub>	700	1000		MHz	$V_{ce} = 10 \text{ V}, I_c = 5 \text{ mA}$
Collector output capacitance	Cob		0.5	0.8	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MI}$
Conversion gain	CG	_	7.0	_	dB	
Noise figure	NF	_	10.0		dB	$V_{cc} = 12 \text{ V}, I_c = 1 \text{ mA}, f = 900 \text{ MHz}, f_{osc} = 930 \text{ MHz} (0\text{dBm}), f_{out} = 30 \text{ MHz}$

Note: Marking is "EC".



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